

22.
21. (Amended) The method according to claim 1, wherein said heating an ion source material comprises heating said indium iodide (InI) at a temperature of not lower than 300 °C and not higher than 380 °C to generate said vapor of said indium iodide (InI).

22. (Amended) A method of generating ions, comprising:
heating an ion source material composed of indium iodide (InI), provided in a longitudinal oven provided outside of an arc chamber, to generate vapor of said indium iodide (InI); and

generating indium (In) ions by discharging said vapor in said arc chamber, wherein a filament is provided on one side surface of said arc chamber, and a reflecting counter electrode is provided on a second side surface of said arc chamber opposite to said one side surface to form an arc in conjunction with said filament, and a gas inlet for said vapor is provided on one face of the arc chamber, said one face being between said one and said second side surfaces and perpendicular thereto, and is configured to introduce said vapor generated in said oven into said chamber almost perpendicularly to said arc.

23.
--24. (New) The method according to claim 1, wherein said ion source material has a particle shape and a particle size of said ion source material not less than 1 mm and not more than 5 mm.

25. (New) The method according to claim 22, wherein said ion source material has a particle shape and a particle size of said ion source material not less than 1 mm and not more than 5 mm.--

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